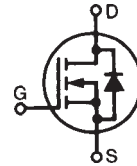


# HiPerFET™ Power MOSFETs Q-CLASS

Single MOSFET Die

N-Channel Enhancement Mode  
Avalanche Rated, Low Q<sub>g</sub>  
High dV/dt, Low t<sub>rr</sub>

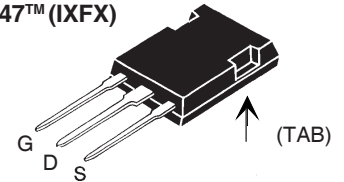


	V <sub>DSS</sub>	I <sub>D25</sub>	R <sub>DS(on)</sub>
IXFK/IXFX 48N50Q	500 V	48 A	100 mΩ
IXFK/IXFX 44N50Q	500 V	44 A	120 mΩ

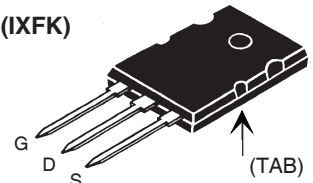
t<sub>rr</sub> ≤ 250 ns

Symbol	Test Conditions	Maximum Ratings	
V <sub>DSS</sub>	T <sub>J</sub> = 25°C to 150°C	500	V
V <sub>DGR</sub>	T <sub>J</sub> = 25°C to 150°C; R <sub>GS</sub> = 1 MΩ	500	V
V <sub>GS</sub>	Continuous	±20	V
V <sub>GSM</sub>	Transient	±30	V
I <sub>D25</sub>	T <sub>C</sub> = 25°C	44N50	44 A
I <sub>DM</sub>	T <sub>C</sub> = 25°C, pulse width limited by T <sub>JM</sub>	48N50	48 A
I <sub>AR</sub>	T <sub>C</sub> = 25°C	44N50	176 A
E <sub>AR</sub>	T <sub>C</sub> = 25°C	48N50	192 A
E <sub>AS</sub>	T <sub>C</sub> = 25°C		48 A
dv/dt	I <sub>S</sub> ≤ I <sub>DM</sub> , di/dt ≤ 100 A/μs, V <sub>DD</sub> ≤ V <sub>DSS</sub> T <sub>J</sub> ≤ 150°C, R <sub>G</sub> = 2 Ω	15	V/ns
P <sub>D</sub>	T <sub>C</sub> = 25°C	500	W
T <sub>J</sub>		-55 ... +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 ... +150	°C
T <sub>L</sub>	1.6 mm (0.063 in.) from case for 10 s	300	°C
M <sub>d</sub>	Mounting torque	TO-264	0.4/6 Nm/lb.in.
Weight		PLUS 247	6 g
		TO-264	10 g

PLUS 247™ (IXFX)



TO-264 AA (IXFK)



G = Gate                      D = Drain  
S = Source                    TAB = Drain

### Features

- IXYS advanced low Q<sub>g</sub> process
- Low gate charge and capacitances
  - easier to drive
  - faster switching
- International standard packages
- Low R<sub>DS(on)</sub>
- Rated for unclamped Inductive load switching (UIS) rated
- Molding epoxies meet UL 94 V-0 flammability classification

### Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls

### Advantages

- PLUS 247™ package for clip or spring mounting
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values (T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
V <sub>DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250μA	500		V
V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 4mA	2.0		4.0 V
I <sub>GSS</sub>	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0			±100 nA
I <sub>DSS</sub>	V <sub>DS</sub> = V <sub>DSS</sub> V <sub>GS</sub> = 0 V T <sub>J</sub> = 125°C			100 μA 2 mA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.5 • I <sub>D25</sub> Note 1	44N50		120 mΩ
		48N50		100 mΩ

Symbol	Test Conditions	Characteristic Values		
		$(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$		
		min.	typ.	max.
$g_{fs}$	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$ Note 1	30	42	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		7000	pF
$C_{oss}$			960	pF
$C_{rss}$			230	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\ \Omega$ (External),		33	ns
$t_r$			22	ns
$t_{d(off)}$			75	ns
$t_f$			10	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		190	nC
$Q_{gs}$			40	nC
$Q_{gd}$			86	nC
$R_{thJC}$			0.26	K/W
$R_{thCK}$		0.15		K/W

Symbol	Test Conditions	Characteristic Values		
		$(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$		
		min.	typ.	max.
$I_S$	$V_{GS} = 0\text{ V}$			48 A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$			192 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}, \text{ Note 1}$			1.5 V
$t_{rr}$	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$			250 ns
$Q_{RM}$			1.0	$\mu\text{C}$
$I_{RM}$			10	A

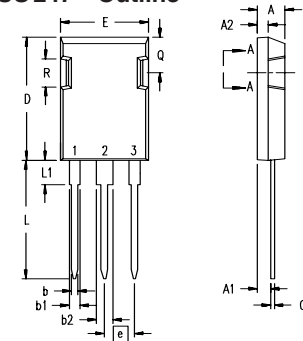
Note: 1. Pulse test,  $t \leq 300\ \mu\text{s}$ , duty cycle  $d \leq 2\%$

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1  
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343

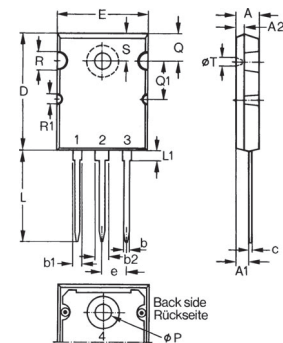
### PLUS 247™ Outline



Terminals: 1 - Gate  
2 - Drain (Collector)  
3 - Source (Emitter)  
4 - Drain (Collector)

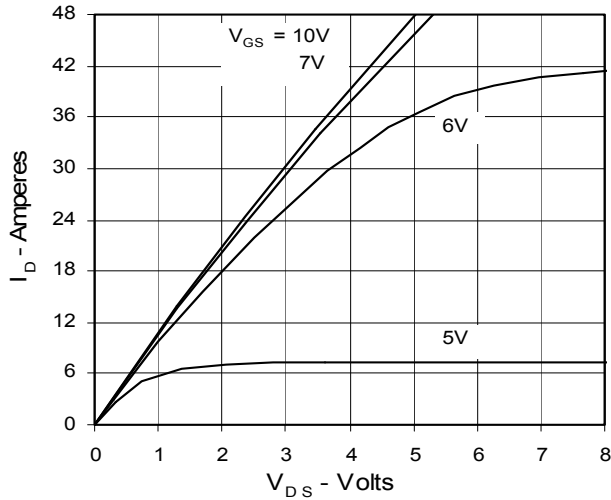
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A <sub>1</sub>	2.29	2.54	.090	.100
A <sub>2</sub>	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b <sub>1</sub>	1.91	2.13	.075	.084
b <sub>2</sub>	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L <sub>1</sub>	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

### TO-264 AA Outline

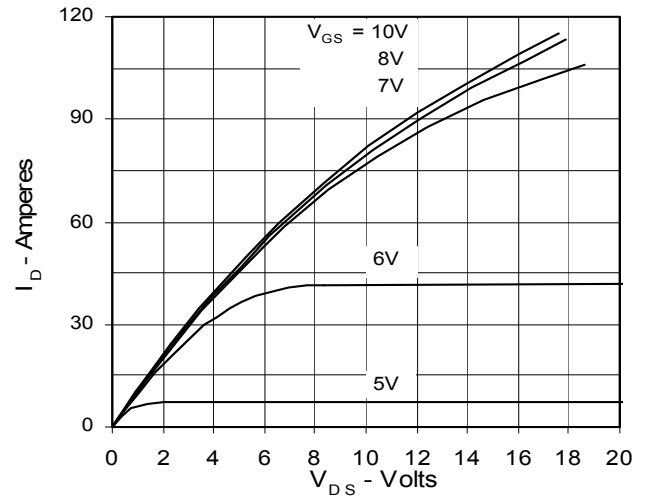


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A <sub>1</sub>	2.54	2.89	.100	.114
A <sub>2</sub>	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b <sub>1</sub>	2.39	2.69	.094	.106
b <sub>2</sub>	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L <sub>1</sub>	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q <sub>1</sub>	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R <sub>1</sub>	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

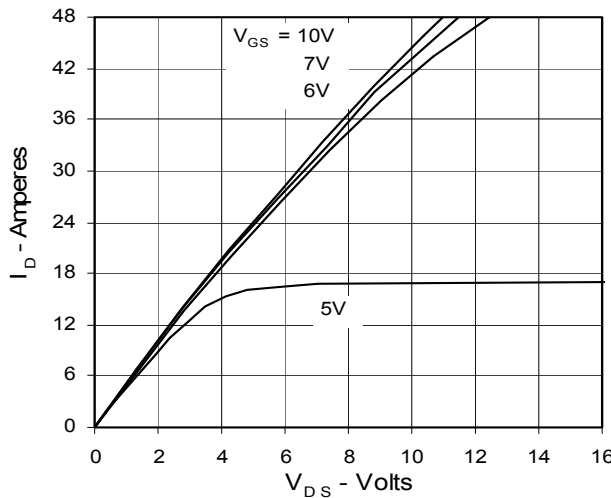
**Fig. 1. Output Characteristics @ 25 Deg. C**



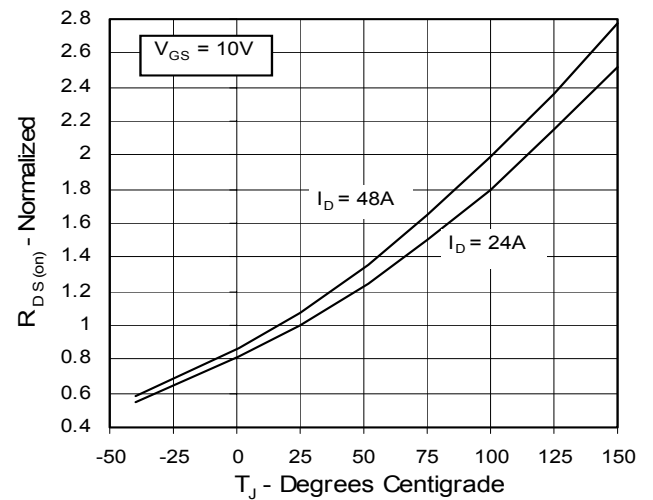
**Fig. 2. Extended Output Characteristics @ 25 deg. C**



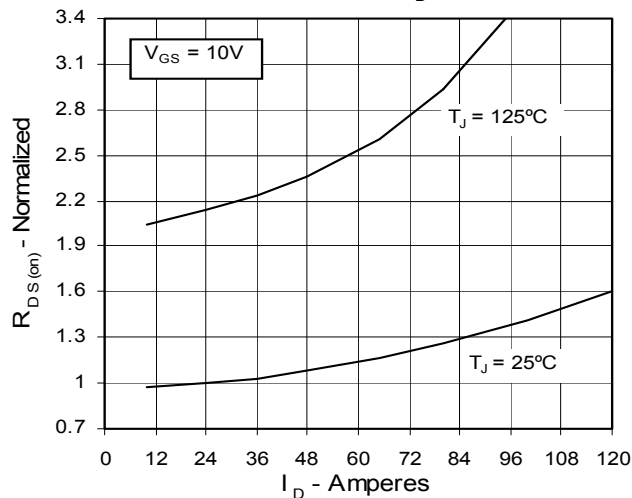
**Fig. 3. Output Characteristics @ 125 Deg. C**



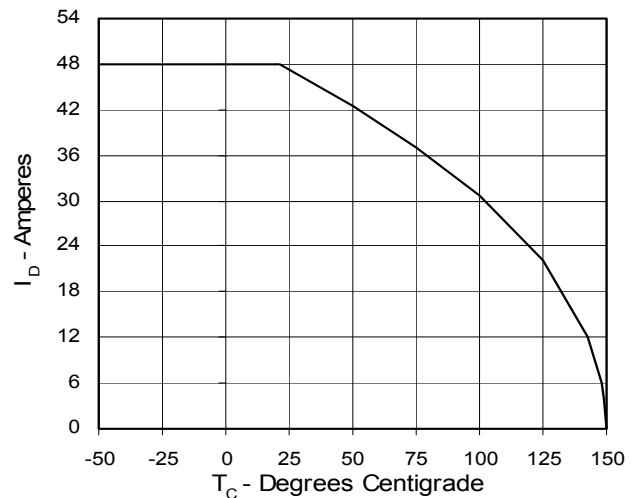
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_{D25}$  Value vs. Junction Temperature**



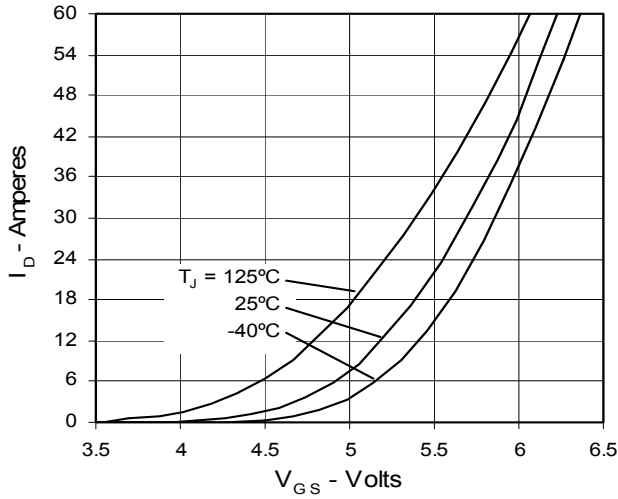
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_{D25}$  Value vs.  $I_D$**



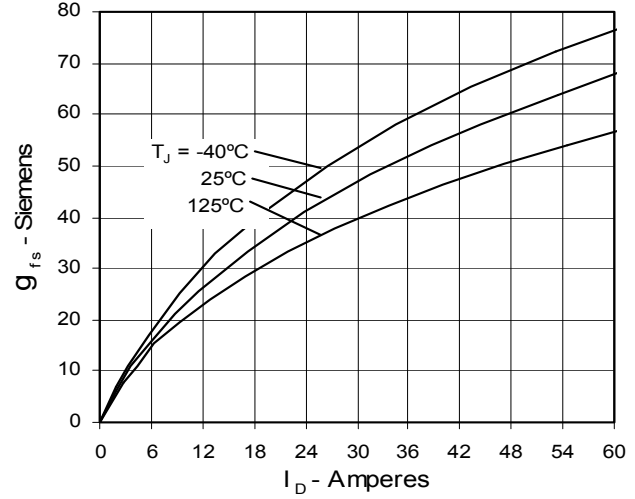
**Fig. 6. Drain Current vs. Case Temperature**



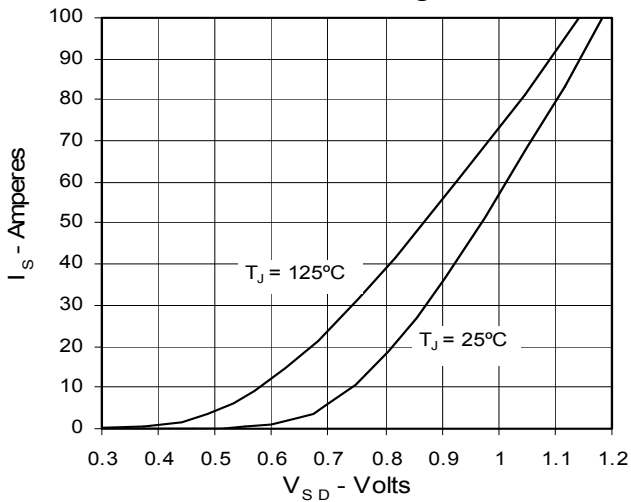
**Fig. 7. Input Admittance**



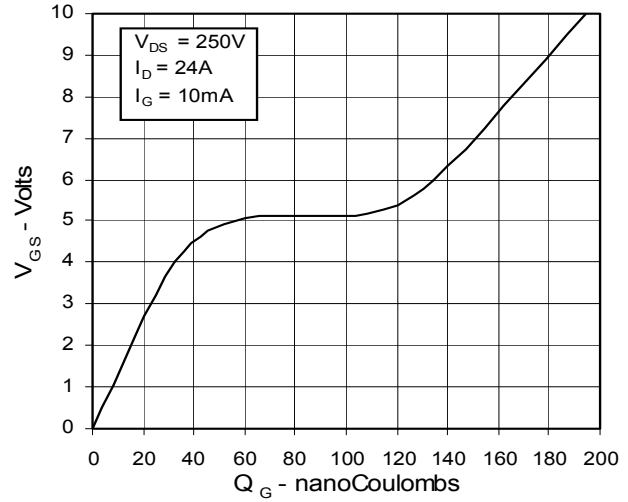
**Fig. 8. Transconductance**



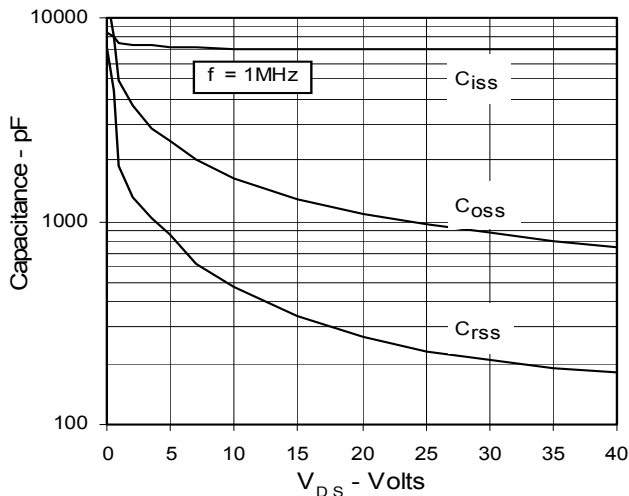
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



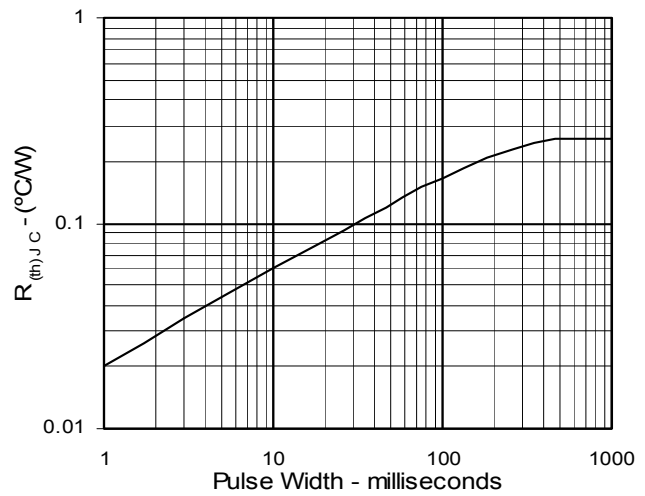
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Resistance**



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